



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SMALL FLAT
NPN Epitaxial Transistor**

VOLTAGE 50 Volts CURRENT 3 Ampere

CHT4672XGP

FEATURE

- * Small flat package. (SC-62/SOT-89)
- * Low saturation voltage $V_{CE(sat)}=0.35V(\text{max.})$
- * High saturation current capability.

CONSTRUCTION

- * NPN Switching Transistor

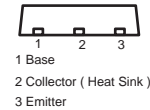
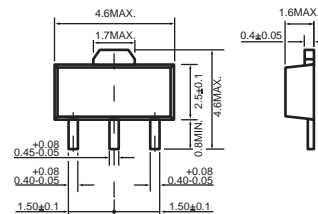
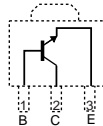
MARKING

- * XHN



SC-62/SOT-89

CIRCUIT



Dimensions in millimeters

SC-62/SOT-89

MAXIMUM RATINGS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

RATINGS	CONDITION	SYMBOL	MIN.	MAX.	UNITS
Collector - Base Voltage	Open Emitter	V_{CBO}	-	50	Volts
Collector - Emitter Voltage	Open Base	V_{CEO}	-	50	Volts
Emitter - Base Voltage	Open Collector	V_{EBO}	-	6	Volts
Collector Current DC		I_C	-	3	Amps
Peak Collector Current Pulse, Note 1		I_{CM}	-	6	Amps
Collector Power Dissipation	$T_A \leq 25^\circ\text{C}$; Note 2	P_{TOT}	-	2	W
Storage Temperature		T_{STG}	-55	+150	$^\circ\text{C}$
Junction Temperature		T_J	-	+150	$^\circ\text{C}$

Note

1. Single pulse, $P_w=10\text{ms}$
2. When mounted on $40 \times 40 \times 0.7\text{mm}$ ceramic board.

2008-06

ELECTRICAL CHARACTERISTIC (CHT4672XGP)

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
BV_{CBO}	collector-base breakdown voltage	$I_E = 0; I_C = 50\text{ }\mu\text{A}$	60	–	V
BV_{CEO}	collector-emitter breakdown voltage	$I_B = 0; I_C = 1\text{ mA}$	50	–	V
BV_{EBO}	emitter-base breakdown voltage	$I_C = 0; I_E = 50\text{ }\mu\text{A}$	6	–	V
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 60\text{ V}$	–	100	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}$ $I_C = 500\text{ mA}$	82	270	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 1000\text{ mA}, I_B = 50\text{ mA}$	–	350	mV
C_C	collector capacitance	$I_E = I_B = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	25 Typ.	pF
f_T	transition frequency	$I_C = 500\text{ mA}; V_{CE} = 2\text{ V};$ $f = 100\text{ MHz}$	–	210 Typ.	MHz

Note :

1. Pulse test: $t_p \leq 300\text{ }\mu\text{Sec}; \delta \leq 0.02.$